

[Name of Document] Abstract

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[Problem]

It is an object to provide a semiconductor memory device having a highly
5 reliable and small-sized involatile memory by realizing a semiconductor memory element
which restrains extreme concentration of an electric field onto a surface of activating
layer in a channel region and is very minute. Further, it is an object thereof to provide a
highly reliable and small-sized semiconductor memory device.

[Means for Resolution]

10 There is fabricated a semiconductor memory element in which a surface of an
activating layer is flat and which is very minute by using a crystallizing process of a
semiconductor activating layer for adding a metal element onto a substrate having an
insulating surface to subject to a heating processing and thereafter carrying out
continuous oscillating laser irradiation. By using such a semiconductor memory
15 element, a highly reliable and small-sized involatile memory and a semiconductor
memory device having the involatile memory are provided.

[Selected Drawing] Fig.1